國立臺灣大學 105 學年度碩士班招生考試試題

題號: 416 科目:電子學(C)

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1. For the circuits shown in Fig. 1, assuming that the opamps are ideal.

- (a) For Fig. 1(a), derive an expression for the differential voltage gain, Vout/Vin. (10%)
- (b) In Fig. 1(b), let $C_2 = C_4 = C$, $C_1 = 10C$, $C_3 = 8C$, and $R_1 = R$, please derive an expression for the differential voltage gain, Vout/Vin. (10%)
- (c) Plot the frequency response of the voltage gain (Vout/Vin) derived in (b). You must denote key parameters in the plot. (10%)

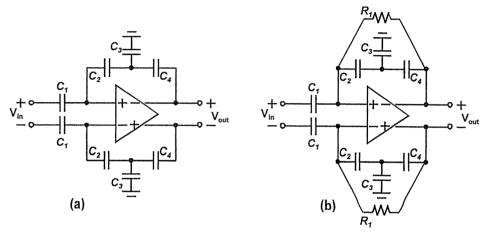
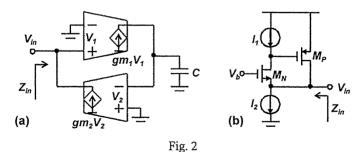


Fig. 1

2. Please refer to Fig. 2.

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- (a) For the circuit of Fig. 2(a), it consists of 2 trans-conductors and a capacitor. Please derive an expression for its input impedance, Z_{in} . What is the purpose of this circuit? (10%)
- (b) For the circuit of Fig. 2(b), assuming V_b , I_l , and I_2 are chosen appropriately such that this circuit is properly biased. Considering transistor parasitic capacitance, but ignoring the channel-length modulation effect, please derive an expression for the input impedance, Z_{in} . (10%)
- (c) Next, derive an expression for the input impedance, Z_{in} , when channel-length modulation effect is considered. How does this affect the circuit performance? (10%)



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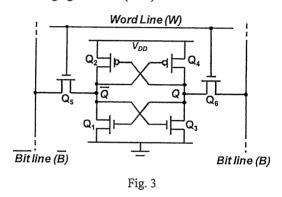
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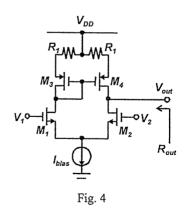
3. Fig. 3 depicts an SRAM cell.

- (a) Describe the **Read** operation of the SRAM cell. Please draw related timing waveforms to assist your description. (5%)
- (b) Describe the Write operation of the SRAM cell. Please draw related timing waveforms to assist your description. (5%)
- (c) How are the sizes of access transistors (Q_5/Q_6), NMOS transistors (Q_1/Q_3), and PMOS transistors (Q_2/Q_4) determined? Please discuss the design guidelines. (10%)



4. Fig. 4 depicts an amplifier circuit.

- (a) Derive expressions for the voltage gain, $V_{out}/(V_2 V_1)$, and the output resistance, R_{out} . (10%)
- (b) This circuit has the following parameters: $I_{bias} = 0.2 \text{ mA}$, $V_{DD} = 3 \text{ V}$, $R_I = 2 \text{ k}\Omega$; NMOS parameters are: $K_n = 4 \text{ mA/V}^2$, $V_{TN} = 1 \text{ V}$, $V_A = 40 \text{ V}$; PMOS parameters are: $K_p = 1 \text{ mA/V}^2$, $V_{TP} = -1 \text{ V}$, $V_A = 25 \text{ V}$. Calculate the voltage gain and output resistance derived in (a). (5%)
- (c) What may be the purpose of adding two resistors (the two R_1) to this circuit? What are the penalties by doing so? (5%)



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